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**April 2014** 

# FGA25N120ANTDTU 1200 V, 25 A NPT Trench IGBT

#### **Features**

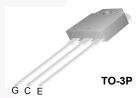
- NPT Trench Technology, Positive Temperature Coefficient
- Low Saturation Voltage: V<sub>CE(sat), typ</sub> = 2.0 V
   Q I<sub>C</sub> = 25 A and T<sub>C</sub> = 25°C
- Low Switching Loss:  $E_{\rm off,\,typ}$  = 0.96 mJ @ I<sub>C</sub> = 25 A and T<sub>C</sub> = 25°C
- Extremely Enhanced Avalanche Capability

### **Applications**

· Induction Heating, Microwave Oven

### **Description**

Using Fairchild's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating, microwave oven.





### **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector-Emitter Voltage		1200	V
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T <sub>C</sub> = 25°C	50	Α
l <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 100°C	25	Α
I <sub>CM (1)</sub>	Pulsed Collector Current		90	Α
	Diode Continuous Forward Current	@ T <sub>C</sub> = 25°C	50	Α
I <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	25	Α
I <sub>FM</sub>	Diode Maximum Forward Current		150	Α
В	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	312	W
$P_D$	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	125	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

#### Notes

(1) Repetitive rating: Pulse width limited by max. junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		0.4	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		2.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

# Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size Tape \		Quantity
FGA25N120ANTDTU_F109	FGA25N120ANTDTU	TO-3PN	Tube	N/A	N/A	30

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V			3	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 250	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 25 mA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	5.5	7.5	V
, ,		I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V		2.0		V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 125°C		2.15		V
		I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15 V	2.65		٧	
Dynamic C	Characteristics					
C <sub>ies</sub>	Input Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$		3700		pF
C <sub>oes</sub>	Output Capacitance	f = 1 MHz		130		pF
C <sub>res</sub>	Reverse Transfer Capacitance			80		pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			50		ns
t <sub>r</sub>	Rise Time			60		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A,		190		ns
t <sub>f</sub>	Fall Time	$R_G = 10 \Omega, V_{GE} = 15 V,$		100		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C		4.1		mJ
E <sub>off</sub>	Turn-Off Switching Loss		/	0.96		mJ
E <sub>ts</sub>	Total Switching Loss		/	5.06		mJ
t <sub>d(on)</sub>	Turn-On Delay Time		/	50		ns
t <sub>r</sub>	Rise Time			60		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A,		200		ns
t <sub>f</sub>	Fall Time	$R_G = 10\Omega$ , $V_{GE} = 15 V$ ,		154		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 125°C		4.3		mJ
E <sub>off</sub>	Turn-Off Switching Loss			1.5		mJ
E <sub>ts</sub>	Total Switching Loss			5.8		mJ
Q <sub>g</sub>	Total Gate Charge			200		nC
Q <sub>ge</sub>	Gate-Emitter Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V		15		nC
Q <sub>gc</sub>	Gate-Collector Charge	VGE - 13 V		100		nC

# Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
	V <sub>FM</sub> Diode Forward Voltage	I <sub>F</sub> = 25 A	T <sub>C</sub> = 25°C		2.0	3.0	V
VFM			T <sub>C</sub> = 125°C		2.1		
	Diede Deverse Desever Time		T <sub>C</sub> = 25°C		235	350	ns
t <sub>rr</sub> Diode Reverse Recovery Time	Diode Reverse Recovery Time		T <sub>C</sub> = 125°C		300		
1	Diode Peak Reverse Recovery Cur-	I <sub>F</sub> = 25 A	T <sub>C</sub> = 25°C		27	40	Α
'rr rent	rent	$di_F/dt = 200 A/\mu s$	T <sub>C</sub> = 125°C		31		A
Q <sub>rr</sub>	Diada Dayaraa Dagayary Charga		T <sub>C</sub> = 25°C		3130	4700	nC
	Diode Reverse Recovery Charge		T <sub>C</sub> = 125°C	125°C 4650		1 IIC	

## **Typical Performance Characteristics**

Figure 1. Typical Output Characteristics

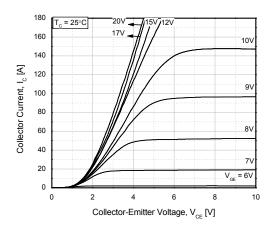


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

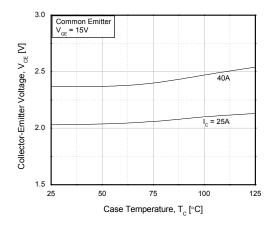


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

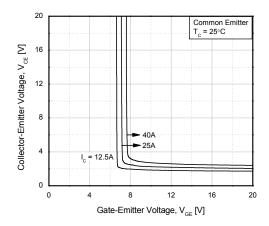


Figure 2. Typical Saturation Voltage Characteristics

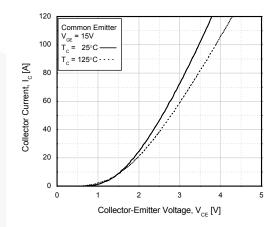


Figure 4. Saturation Voltage vs. V<sub>GE</sub>

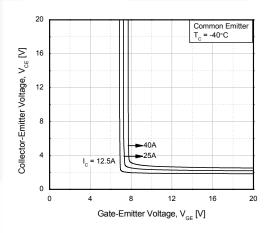
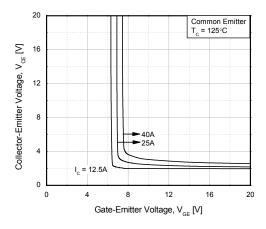


Figure 6. Saturation Voltage vs. V<sub>GE</sub>



## Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

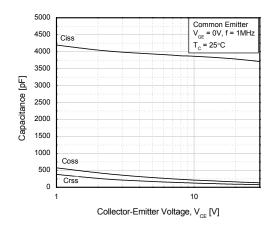


Figure 8. Turn-On Characteristics vs. Gate Resistance

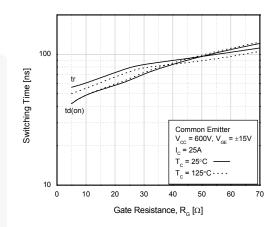


Figure 9. Turn-Off Characteristics vs.
Gate Resistance

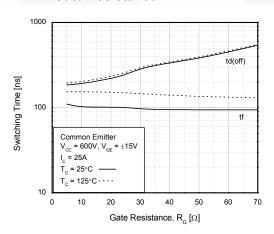


Figure 10. Switching Loss vs. Gate Resistance

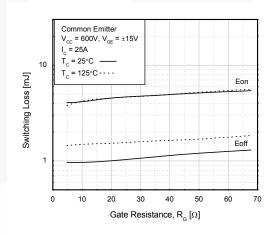


Figure 11. Turn-On Characteristics vs. Collector Current

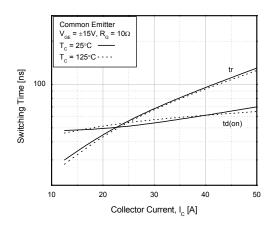
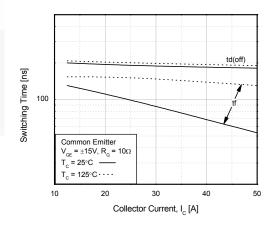
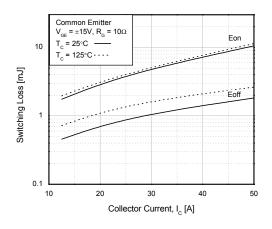


Figure 12. Turn-Off Characteristics vs. Collector Current



## Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current



Common Emitter

14

R<sub>L</sub> = 24Ω

T<sub>C</sub> = 25°C

Vcc = 200V

600V

400V

Gate Charge, Q [nC]

Figure 14. Gate Charge Characteristics

Figure 15. SOA Characteristics

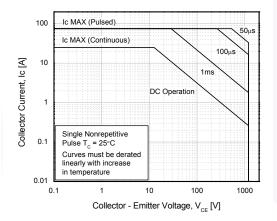


Figure 16. Turn-Off SOA

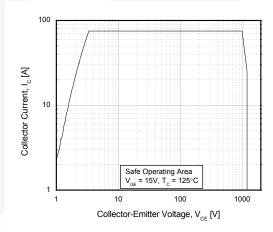
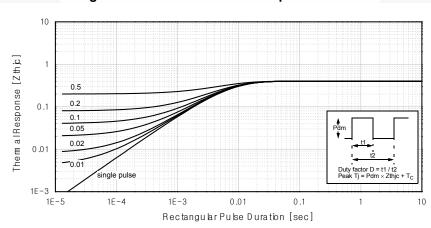


Figure 17. Transient Thermal Impedance of IGBT



## **Typical Performance Characteristics** (Continued)

### Figure 18. Forward Characteristics

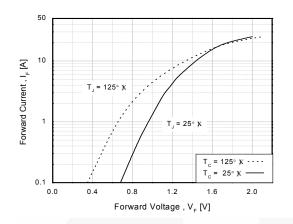
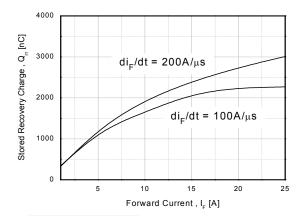


Figure 20. Stored Charge



**Figure 19. Reverse Recovery Current** 

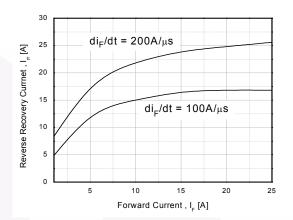
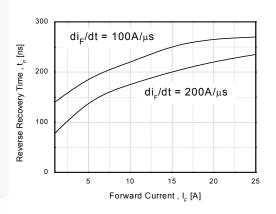
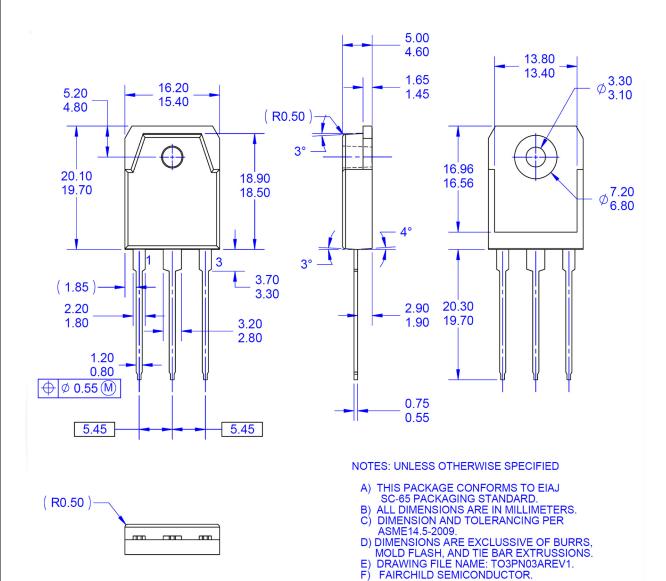


Figure 21. Reverse Recovery Time



#### **Mechanical Dimensions**



### Figure 22. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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